1 Scope

The present specifications shall apply to a RH1C.

2 Outline

Туре	Silicon Diode			
Structure	Resin Molded Flammability:UL94-V0(Equivalent)			
Applications	High Frequency Rectification, etc.			

3 Absolute maximum ratings

B Abso	olute maximum ratings	Ś			
No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V _{RSM}	V	1000	
2	Peak Reverse Voltage	V _{RM}	V	1000	
3	Average Forward Current	$I_{F(AV)}$	А	0.6	Refer to derating curve in Section 6
4	Peak Surge Forward Current	I _{FSM}	А	35	10ms. Half sine wave, one shot
5	I ² t Limiting Value	I ² t	A ² s	6.125	$1 \text{ ms} \leq t \leq 10 \text{ ms}$
6	Junction Temperature	Tj	°C	-40 to +150	
7	Storage Temperature	T _{stg}	°C	-40 to +150	

4 Electrical characteristics (Ta=25°C, unless otherwise specified)

No.	Item	ymbol	Unit	Value	Conditions
1	Forward Voltage Drop	\mathbf{V}_{F}	V	1.3 max.	I _F =0.6A
2	2 Reverse Leakage Current		μΑ	5 max.	V _R =V _{RM}
3	Reverse Leakage Current Under High Temperature	H•I _R	μΑ	70 max.	$V_R=V_{RM}, T_a=100^{\circ}C$
4	4 Reverse Recovery Time		μs	4.0 max.	I _F =I _{RP} =10mA 90% Recovery point, T _j =25°C
	Reverse Recovery Time	Trr-2	μs	1.3 max.	I _F =100mA, I _R =200mA 75% Recovery point ,T _j =25°C
5	Thermal Resistance	Rth (j-l)	°C /W	15 max.	Between Junction and Lead



